# 2SK3289

# Silicon N Channel MOS FET High Speed Switching

# **HITACHI**

ADE-208-743C (Z) 4th.Edition. June 1999

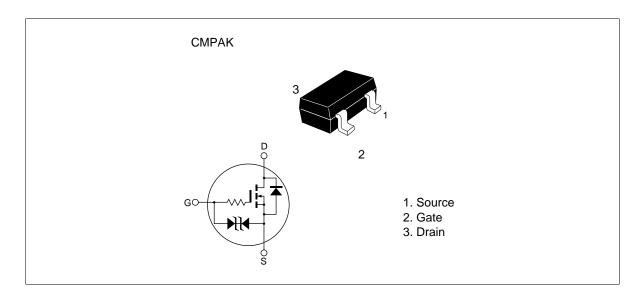
#### **Features**

• Low on-resistance

$$R_{DS}$$
 =1.26  $\Omega$  typ. (V  $_{GS}$  = 10 V ,  $I_D$  = 150 mA) 
$$R_{DS}$$
 = 2.8  $\Omega$  typ. (V  $_{GS}$  = 4 V ,  $I_D$  = 50 mA)

- 4 V gate drive device.
- Small package (CMPAK)

#### **Outline**





# 2SK3289

### **Absolute Maximum Ratings** (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	30	V
Gate to source voltage	V <sub>GSS</sub>	±20	V
Drain current	I <sub>D</sub>	300	mA
Drain peak current	Note1	1.2	A
Body-drain diode reverse drain current	I <sub>DR</sub>	300	mA
Channel dissipation	Pch Note 2	300	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

2. Value on the alumina ceramic board (12.5 x 20 x 0.7 mm)

### **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

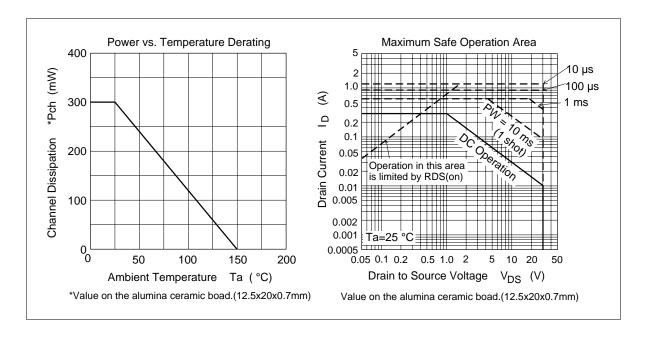
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	_	_	V	$I_D = 100  \mu A,  V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	_	_	V	$I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±5	μΑ	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltege drain current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 30 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{\rm GS(off)}$	1.3	_	2.3	V	$I_{D} = 10\mu A, V_{DS} = 5 V$
Static drain to source on state		_	1.26	3.44	Ω	$I_D = 150 \text{ mA}, V_{GS} = 10 \text{ V}^{\text{Note 3}}$
resistance	R <sub>DS(on)</sub>	_	2.8	3.44	Ω	$I_D = 50 \text{ mA}, V_{GS} = 4 \text{ V}^{\text{Note 3}}$
Forward transfer admittance	y <sub>fs</sub>	145	220	_	mS	$I_D = 150 \text{ mA}, V_{DS} = 10 \text{ V}^{\text{Note 3}}$
Input capacitance	Ciss	_	6	_	pF	V <sub>DS</sub> = 10 V
Output capacitance	Coss	_	18	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	2	_	pF	f = 1 MHz
Turn-on delay time	t <sub>d(on)</sub>	_	200	_	ns	$I_D = 150 \text{ mA}, V_{GS} = 10 \text{ V}$
Rise time	t <sub>r</sub>	_	600	_	ns	$R_L = 66.6 \Omega$
Turn-off delay time	$t_{d(off)}$	_	1100	_	ns	_
Fall time	t <sub>f</sub>	_	1100	_	ns	_

Note: 3. Pulse test

4. Marking is AN

See characteristics curves of 2SK3287

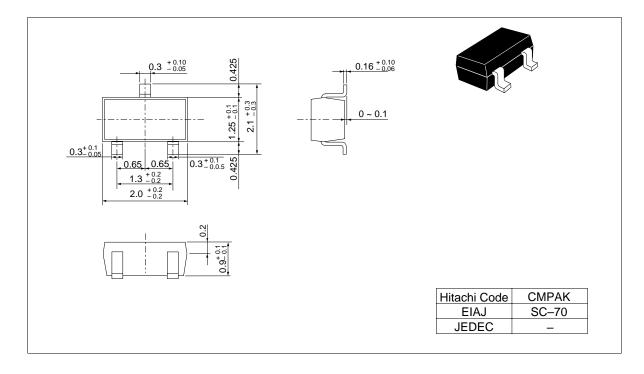
### **Main Characteristics**



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# **Package Dimensions**

Unit: mm



#### **Cautions**

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